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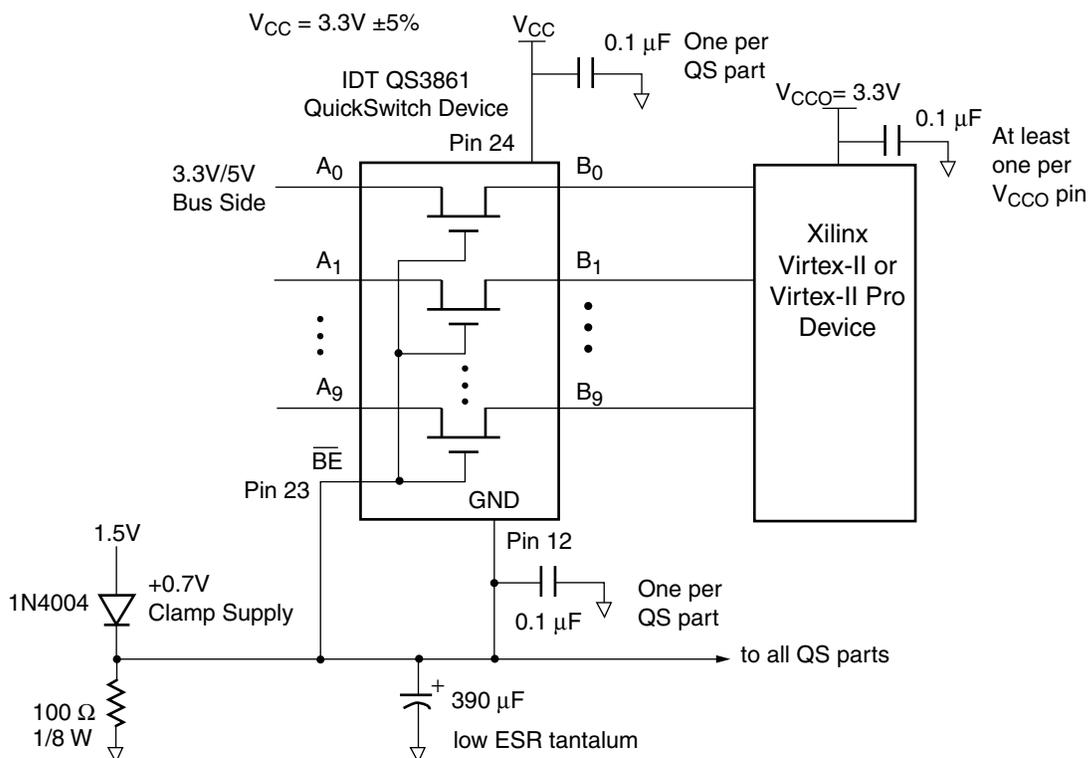
Connecting Virtex-II Devices to a 3.3V/5V PCI Bus

Summary

This application note describes how to connect Virtex™-II and Virtex-II Pro™ devices to 3.3V or 5V PCI buses. The design responds to customer demand for a general solution for applications with a Virtex-II device and a 5V PCI bus, as well as for applications with a Virtex-II Pro device and a 3.3V or 5V PCI bus.

3.3V/5V Universal PCI Implementation

In **Figure 1**, the IDT QuickSwitch® device is in series with the signals of a 3.3V or 5V bus. The delay is roughly 250 ps, and the loading is less than 5 pF, so the device does not affect the bus timing. Since the device is a set of series-connected NMOS transistors, any voltage larger than a few hundred millivolts below the V_{CC} pin voltage will be cutoff.



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Figure 1: QuickSwitch to Virtex-II/Virtex-II Pro Connection

The NMOS transistors are in the P-well of the substrate and have intrinsic diodes to the ground pin of the device. By biasing the ground pin at $\sim 0.7 V_{DC}$, the undershoot is clamped, and the lowest voltage at the Virtex-II Pro device is perhaps only a few hundred millivolts less than ground.

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The B side of the QuickSwitch device will limit the positive overshoot voltage from the A side to less than ~3.0V, and also limit the negative undershoot excursions (undershoot) to not more than -0.1 volt.

The 0.1 μ F bypass capacitor from V_{CC} to ground (one each per QuickSwitch device), and the 0.1 μ F bypass capacitor from the ground pin bias point to the system ground are required to absorb the transients and provide a good clamping and cutoff action.

The 0.7V bias supply is easily generated by a forward biased diode from the V_{CCINT} 1.5V supply. The large tantalum (or low ESR aluminum electrolytic) may be required to keep this voltage stable over all possible bus activity duty cycles. The pull-down resistor sets the maximum bias supply voltage at ~0.9V DC. Up to four QuickSwitch devices can be biased from this supply to support the 66/64-bit PCI bus, for example.

The undershoot current is roughly 10 mA average per pin, so that the supply with the 1A diode easily can provide the necessary current (about 0.66A, worst case).

Bypassing the Virtex device at less than 35 mm (<1.4 inches) is also key to providing a good interface.

For more information about PCI implementation, refer to the Virtex-II or Virtex-II Pro User Guides and other Xilinx documentation.

IDT QuickSwitch Technology

In its basic form, the QuickSwitch technology is an N-channel FET switch controlled by either combinatorial or sequential control logic using CMOS technology. **Figure 2** shows the basic QuickSwitch configuration.

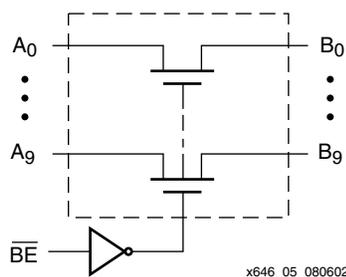


Figure 2: Basic QuickSwitch Configuration

When the switch is enabled, the gate of the N-channel switch transistor driven by a CMOS logic gate is at V_{CC} and the switch exhibits a typical ON resistance of 5 Ω . The series resistance will be higher than 5 Ω when V_{CC} supply is 3.3V and port A is driven by 5V. Consider the QS3R861 if a lower ON resistance is desired. When disabled, the gate of the switch is at ground potential and the switch offers very high resistance between the A and B terminals. In the OFF state, the leakage current at the switch terminals is typically 10 nA, and the capacitance between the terminals is low. Typical capacitance at the switch terminals is 5 pF in the OFF state.

QuickSwitch devices are available from IDT with an estimated 1K volume price of about \$0.30 each for the SO and Q packages, and \$0.75 for the PA package. **Table 1** shows the part numbers and dimensions of each package.

Table 1: QuickSwitch Package Information

Part Number	Length x Width x Thickness (mm)
IDTQS3861SO (Small-Outline Package)	15.4 x 7.5 x 2.34
IDTQS3861Q (Quarter Size Outline Package)	8.7 x 3.8 x 1.47
IDTQS3861PA (Thin-Shrink Small-Outline Package)	7.8 x 4.4 x 1.0

For more information on QuickSwitch devices, refer to:
http://www.idt.com/products/pages/Bus_Switches-QS3861.html

Revision History

The following table shows the revision history for this document.

Date	Version	Revision
06/17/02	1.0	Initial Xilinx release.
08/01/02	1.1	Revised Figure 1 for clarification.
08/08/02	1.2	Revised Figure 1 for clarification, revised text with regards to QuickSwitch devices.